

APPLICATION NOTE

# Characterization of Surface Contamination

## DISCUSSION

Elemental characterization of defects and contamination on surfaces is a necessity for failure analysis. Energy Dispersive X-Ray Spectrometry (EDS), combined with Scanning Electron Microscopy (SEM) provides a rapid and efficient tool for characterizing particles and defects which are on the order of  $1\mu\text{m}$  or larger. Modern instruments allow for the detection of light elements (B through F), as well as the higher Z elements, and for simultaneous imaging of multiple elements. The lateral distribution of seven elements is shown in Figure 1 along with secondary electron and back-scattered electron images. From this collection of images it is readily determined that the contamination is a conglomeration of carbon bearing material and oxides of Mg, Al and Si.

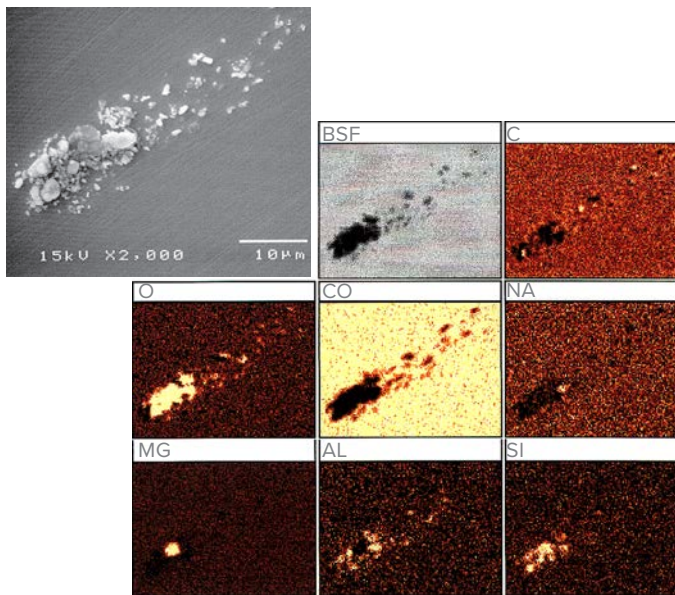


Figure 1: Secondary Electron Image (SEI) of the surface defect and associated EDS elemental images and back-scattered electron image.

For particles and defects smaller than 1 micron, an ideal tool is Auger Electron Spectroscopy (AES). With this instrument, features as small as  $200\text{\AA}$  can be characterized elementally. An example is given in Figure 2. The Auger survey spectrum of a  $500\text{\AA}$  particle on a silicon wafer reveals the particle contains aluminum.

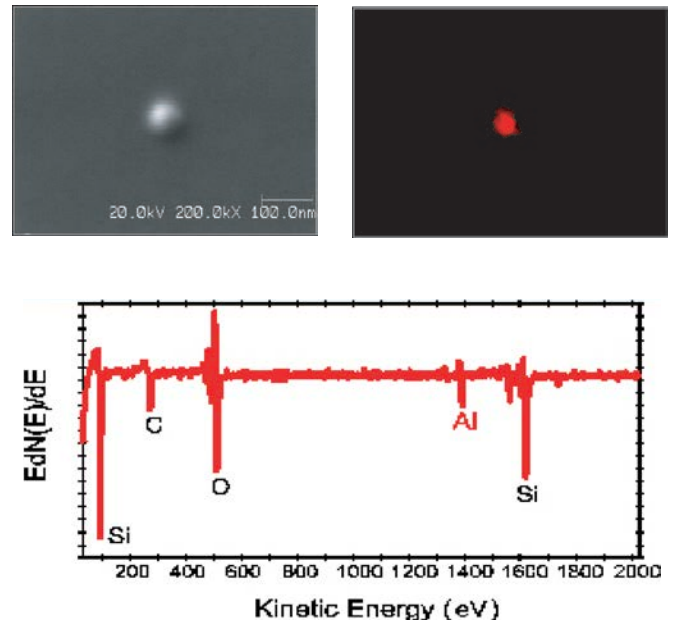


Figure 2: Auger survey spectrum (bottom) of the  $500\text{\AA}$  particle shown in the secondary electron image (top-left) reveals aluminum contamination. The Al map is shown in the top right.